

### 6 - 12 GHz 30 W GaN Power Amplifier

### **Product Description**

Qorvo's TGA2590-CP is a wideband MMIC power amplifier fabricated on Qorvo's QGaN25 0.25um GaN on SiC process. The TGA2590-CP operates from 6-12GHz and provides 30W of saturated output power with >22dB of large signal gain and >30% power-added efficiency.

The TGA2590-CP is offered in a 10-lead 15 x 15 mm bolt-down package. The package has a pure Cu base, offering superior thermal management.

The TGA2590-CP is fully matched to  $50\,\Omega$  with DC blocking caps at both RF ports allowing for simple system integration. The broadband performance supports both electronic warfare and radar opportunities across defense and commercial markets.

Lead-free and RoHS compliant.



### **Product Features**

• Frequency Range: 6-12 GHz

• Pout: 45 dBm @ PiN = 23 dBm

• PAE: >30% @ P<sub>IN</sub> = 23 dBm

• Small Signal Gain: 35 dB

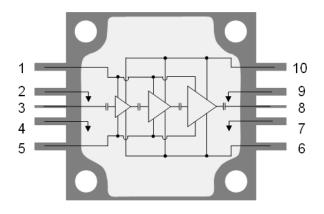
• Bias:  $V_D = +20 \text{ V (CW)}$ ,  $I_{DQ} = 2 \text{ A}$ ,  $V_G = -2.4 \text{ V typical}$ 

• Package Dimensions: 15.2 x 15.2 x 3.5 mm

Package base is pure Cu offering superior thermal management

Performance is typical across frequency. Please reference electrical specification table and data plots for more details

# **Functional Block Diagram**



# **Applications**

- · Electronic Warfare
- · Commercial and Military Radar

# **Ordering Information**

Part No.	Description		
TGA2590-CP	6 – 12 GHz 30 W GaN Power Amplifier		
1098063	TGA2590-CP Evaluation Board		



### 6 - 12 GHz 30 W GaN Power Amplifier

### **Absolute Maximum Ratings**

Parameter	Value / Range
Drain Voltage (V <sub>D</sub> )	40 V
Gate Voltage Range (V <sub>G</sub> )	-8 to 0 V
Drain Current (I <sub>D</sub> )	8 A
Gate Current (I <sub>G</sub> )	See plot page 6
Power Dissipation (P <sub>DISS</sub> ), 85°C	135 W
Input Power (P <sub>IN</sub> ), 50Ω, 85°C, CW	30 dBm
Input Power (P <sub>IN</sub> ), 85°C, VSWR 6:1, VD = 20V, CW	27 dBm
Lead Soldering Temperature (30 Seconds)	260°C
Storage Temperature	−55 to 150 °C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

## **Recommended Operating Conditions**

Parameter	Min	Тур.	Max	Units
Drain Voltage (V <sub>D</sub> )	+20		+25	V
Drain Current, (IDQ)		2		Α
Gate Voltage Range (V <sub>G</sub> )		-2 to -3		V
Input Power (P <sub>IN</sub> )	+17		+25	dBm
T <sub>BASE</sub> Range	-40		+85	۰C
E1 (1 1 20 C)		1 .		

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

## **Electrical Specifications**

Parameter	Min	Тур	Max	Units
Operational Frequency Range	6		12	GHz
Small Signal Gain	-	35	-	dB
Input Return Loss	-	5	-	dB
Output Return Loss	-	5	-	dB
Output Power (@ P <sub>IN</sub> = 23 dBm)	-	46	-	dBm
Power Added Efficiency (@ P <sub>IN</sub> = 23 dBm)	-	>30	-	%
Drain Voltage (V <sub>D</sub> )	20	-	25	V
Load VSWR	-	-	2.0:1	
Input Power (P <sub>IN</sub> )	17	-	25	dBm
Small Signal Gain Temperature Coefficient		-0.07		dB/°C
Output Power Temperature Coefficient		-0.015		dBm/°C

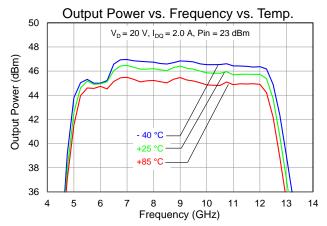
Test conditions unless otherwise noted:  $25 \,^{\circ}$ C,  $V_D = +20 \,\text{V}$ ,  $I_{DQ} = 2 \,\text{A}$ ,  $V_G = -2.4 \,\text{V}$  typical, CW.

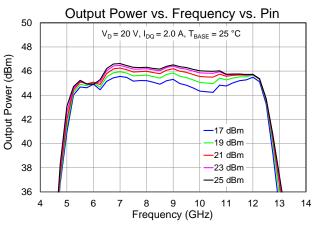


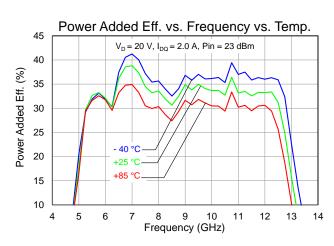
## 6 - 12 GHz 30 W GaN Power Amplifier

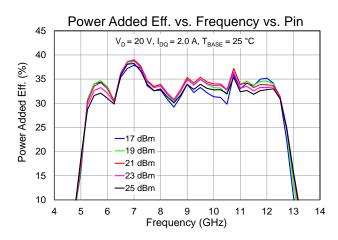
### Typical Performance - Large Signal

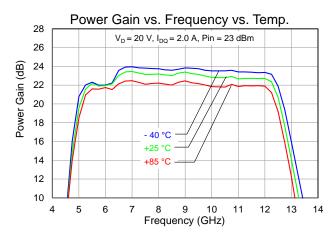
Conditions unless otherwise specified:  $V_D = 20 \text{ V}$ ,  $I_{DQ} = 2 \text{ A}$ ,  $V_G = -2.4 \text{ V}$  Typical, CW.

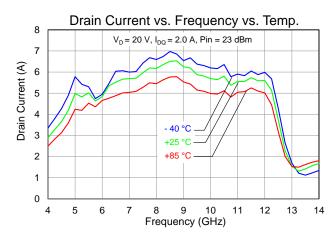










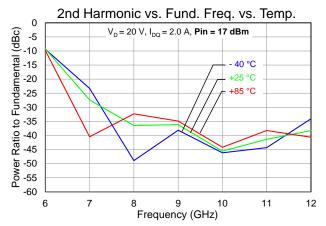


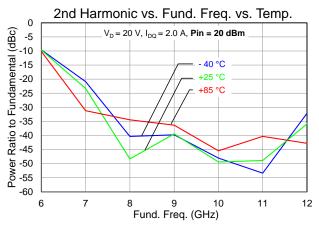


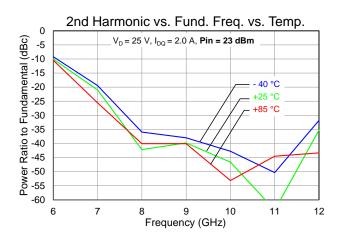
### 6 - 12 GHz 30 W GaN Power Amplifier

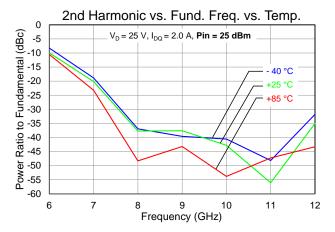
### **Typical Performance – Large Signal (Harmonics)**

Conditions unless otherwise specified:  $V_D = 20 \text{ V}$ ,  $I_{DQ} = 2 \text{ A}$ ,  $V_G = -2.4 \text{ V}$  Typical, CW.



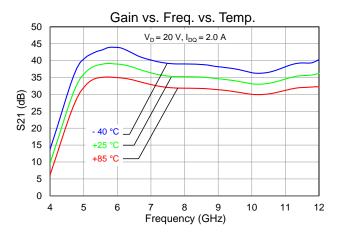


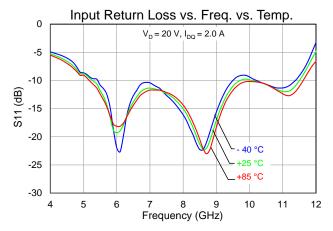


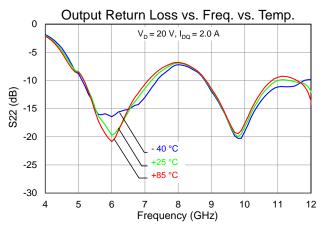


# Performance Plots - Small Signal (CW)

Conditions unless otherwise specified:  $V_D = 20 \text{ V}$ ,  $I_{DQ} = 2 \text{ A}$ ,  $V_G = -2.4 \text{ V}$  Typical, CW.







### 6 - 12 GHz 30 W GaN Power Amplifier

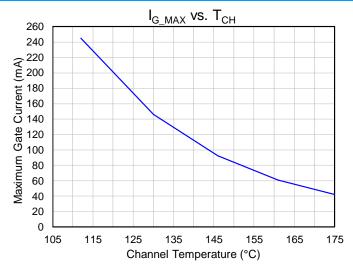
### **Thermal and Reliability Information**

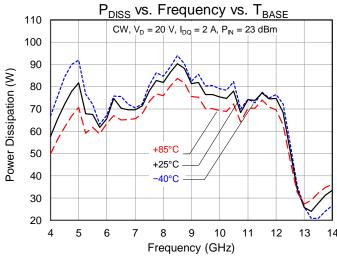
Parameter	Test Conditions	Value	Units
Thermal Resistance (θ <sub>JC</sub> ) <sup>(1)</sup>	V <sub>D</sub> = 20 V, I <sub>DQ</sub> = 2 A, Freq. = 8.5 GHz	0.81	°C/W
Channel Temperature, T <sub>CH</sub> (Under RF) (2)	$\begin{array}{c} T_{base} = 85 \ ^{\circ}\text{C}, \ V_{D} = 20 \ \text{V}, \ I_{D\_Drive} = 5.8 \ \text{A}, \\ P_{IN} = 23 \ dBm, \ P_{OUT} = 45 \ dBm, \ P_{DISS} = 83.8 \ W \end{array}$	153	°C

#### Notes:

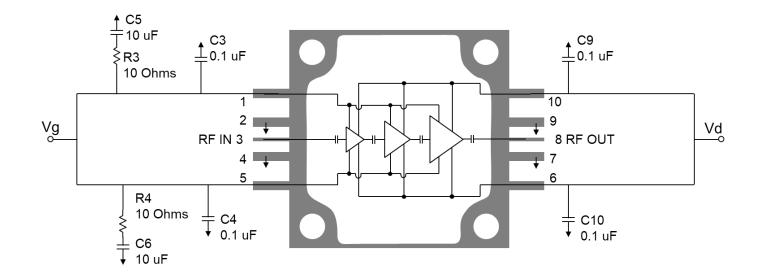
- 1. Thermal resistance is referenced to the back of package (85 °C)
- 2. Refer to the following document: GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates

# **Dissipated Power and Maximum Gate Current**





# **Applications Information and Pin Layout**



#### Notes:

- 1. V<sub>G</sub> must be biased from both sides (Pins 1 and 5)
- 2.  $V_D$  must be biased from both sides (Pins 6 and 10)

### **Bias Up Procedure**

1. Set I <sub>D</sub> limit to 8 A, I <sub>G</sub> limit to 200 mA
2. Apply -5 V to V <sub>G</sub>
3. Apply 20 V to V <sub>D</sub> ; ensure I <sub>DQ</sub> is approx. 0 mA
4. Adjust $V_G$ until $I_{DQ} = 2$ A ( $V_G \sim -2.4$ V Typ.).

5. Turn on RF supply

### **Bias Down Procedure**

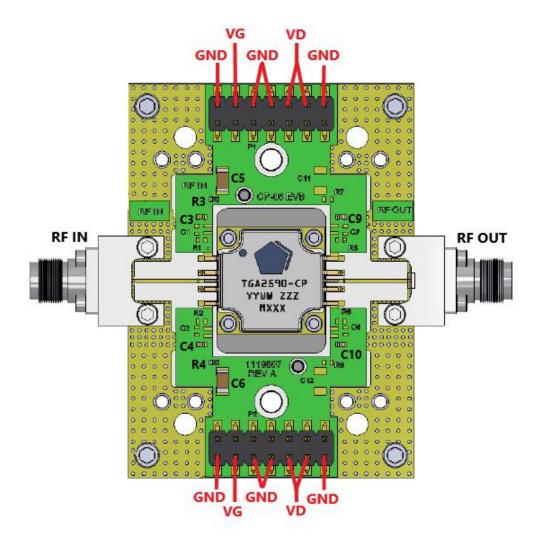
1. Turn off RF supply
2. Reduce V <sub>G</sub> to −5 V; ensure I <sub>DQ</sub> is approx. 0 mA
3. Set V <sub>D</sub> to 0 V
4. Turn off V <sub>D</sub> supply
5. Turn off V <sub>G</sub> supply

### **Pin Description**

Pad No.	Symbol	Description	
1,5	V <sub>G</sub>	Gate Voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.	
2,4,7,9	GND	Must be grounded on the PCB.	
3	RFIN	Input; matched to 50 Ω; DC blocked	
6,10	VD	Drain voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.	
8	RF <sub>OUT</sub>	Output; matched to 50 Ω; DC blocked.	

# 6 - 12 GHz 30 W GaN Power Amplifier

### **Evaluation Board (EVB) Assembly Drawing**



#### PCB NOTES:

- 1. PCB is made from Rogers 4003C dielectric, 0.008 inch thick, 0.5 oz. copper both sides.
- 2. Both Top and Bottom  $V_{\text{\scriptsize D}}$  and  $V_{\text{\scriptsize G}}$  must be biased.

### **Bill of Materials**

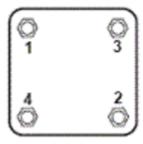
Reference Des.	Value	Description	Manuf.	Part Number
C3, C4, C9, C10	0.1 µF	Cap, 0402, 50 V, 10%, X7R	Various	_
C5, C6	10 uF	Cap, 1206, 50 V, 20%, X5R	Various	_
R3, R4	10 Ω	Res, 0402, 5%	Various	_



### 6 - 12 GHz 30 W GaN Power Amplifier

### **Assembly Notes**

- 1. Carefully clean the PC board and package leads with alcohol. Allow it to dry fully.
- To improve the thermal and RF performance, Qorvo recommends attaching a heat sink to the bottom of the PCB and apply thermal compound (Arctic Silver 5 recommended) or 4 mil indium shim between the heat sink and the package.
- 3. (The following is for *information only*. There are many variables in a second level assembly that Qorvo does not control, so Qorvo does not recommend an absolute torque value.) Use screws to attach the component to the heat sink. A suggested torque value is 16 in-oz. for a 0-80 screw. Start with screws finger tight, then torque to 8 in-oz., then torque to final value. Use the following tightening pattern:



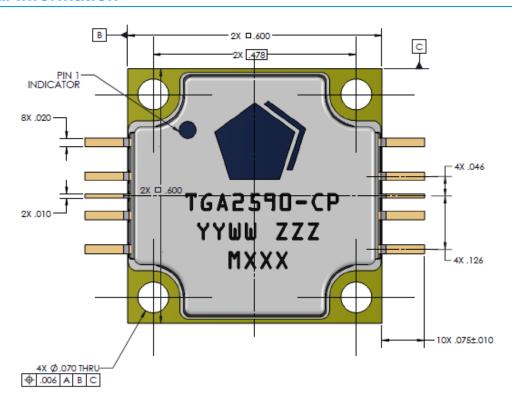
4. Apply no-flux solder to each pin of the TGA2590-CP. The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. The use of no-clean solder to avoid washing after soldering is recommended.





# 6 - 12 GHz 30 W GaN Power Amplifier

### **Mechanical Information**





Units: inches

Tolerances: unless specified

 $x.xx = \pm 0.01$  $x.xxx = \pm 0.005$ 

Materials:

Lid: Liquid Crystal Polymer (LCP)

Leads: Alloy 194 Base: Copper

Finish: All metalized features are gold plated; part is epoxy sealed

Marking:

TGA2590-CP: Part number

YY: Part assembly year WW: Part assembly week ZZZ: Serial number MXXX: Batch ID



### 6 – 12 GHz 30 W GaN Power Amplifier

### **Handling Precautions**

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1B	JEDEC Standard JESD22 A114
ESD-Charge Device Model (CDM)	Class C3	JEDEC Standard JESD22-C101F
MSL – Moisture Sensitivity Level	N/A	



### **Solderability**

The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. Soldering of the component leads is compatible with the latest version of J-STD-020, lead-free solder, 260 °C. The use of no-clean solder to avoid washing after soldering is recommended.

### **RoHS Compliance**

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C<sub>15</sub>H<sub>12</sub>Br<sub>4</sub>O<sub>2</sub>) Free
- PFOS Free
- SVHC Free

### Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: <u>www.qorvo.com</u>
Tel: 1-844-890-8163

Email: <u>customer.support@gorvo.com</u>

### **Important Notice**

The information contained herein is believed to be reliable; however, Qorvo makes no warranties regarding the information contained herein and assumes no responsibility or liability whatsoever for the use of the information contained herein. All information contained herein is subject to change without notice. Customers should obtain and verify the latest relevant information before placing orders for Qorvo products. The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information. THIS INFORMATION DOES NOT CONSTITUTE A WARRANTY WITH RESPECT TO THE PRODUCTS DESCRIBED HEREIN, AND QORVO HEREBY DISCLAIMS ANY AND ALL WARRANTIES WITH RESPECT TO SUCH PRODUCTS WHETHER EXPRESS OR IMPLIED BY LAW, COURSE OF DEALING, COURSE OF PERFORMANCE, USAGE OF TRADE OR OTHERWISE, INCLUDING THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE.

Without limiting the generality of the foregoing, Qorvo products are not warranted or authorized for use as critical components in medical, life-saving, or life-sustaining applications, or other applications where a failure would reasonably be expected to cause severe personal injury or death.

Copyright 2019 © Qorvo, Inc. | Qorvo is a registered trademark of Qorvo, Inc.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Qorvo:

TGA2590-CP